XC61F Series

Voltage Detectors, Delay Circuit Built-In

■GENERAL DESCRIPTION

The XC61F series are highly accurate, low power consumption voltage detectors, manufactured using CMOS and laser trimming technologies. A delay circuit is built-in to each detector.
Detect voltage is extremely accurate with minimal temperature drift.
Both CMOS and N-channel open drain output configurations are available.
Since the delay circuit is built-in, peripherals are unnecessary and high density mounting is possible.

■APPLICATIONS

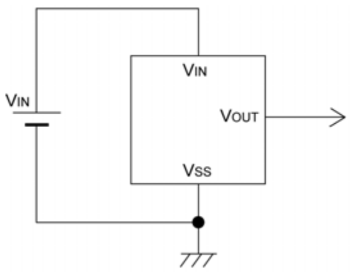
●Microprocessor reset circuitry
●Memory battery back-up circuits
●Power-on reset circuits
●Power failure detection
●System battery life and charge voltage monitors
●Delay circuitry

■FEATURES

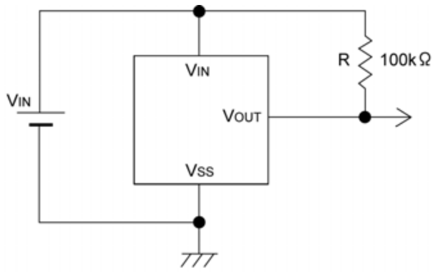
Highly Accurate : ± 2%
Low Power Consumption : 1.0 μA (TYP.)[V_{IN}=2.0V]
Detect Voltage Range : 1.6V ~ 6.0V in 0.1V increments
Operating Voltage Range : 0.7V ~ 10.0V
Detect Voltage Temperature Characteristics : ±100ppm/℃(TYP.)
Built-In Delay Circuit : ① 1ms ~ 50ms
② 50ms ~ 200ms
③ 80ms ~ 400ms
Output Configuration : N-channel open drain or CMOS
Packages : SOT-23
: SOT-89
: TO-92

* No parts are available with an accuracy of ± 1%

■TYPICAL APPLICATION CIRCUITS



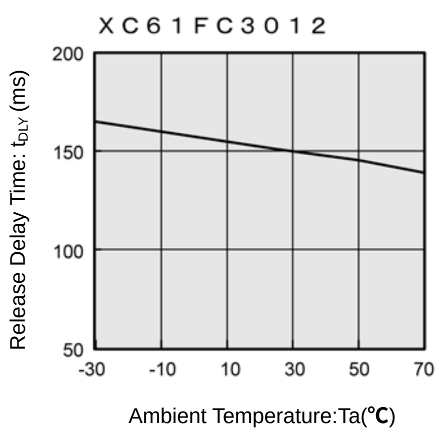
CMOS output



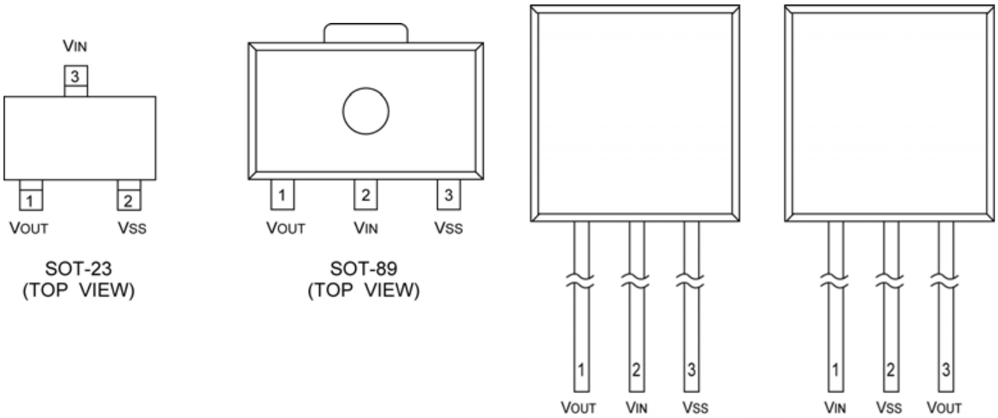
N-channel open drain output

■TYPICAL PERFORMANCE CHARACTERISTICS

●Release Delay Time vs. Ambient Temperature



■PIN CONFIGURATION



SOT-23 (TOP VIEW)

SOT-89 (TOP VIEW)

TO-92 (T Type) (SIDE VIEW)

TO-92 (L Type) (SIDE VIEW)

■PIN ASSIGNMENT

PIN NUMBER				PIN NAME	FUNCTION
SOT-23	SOT-89	TO-92 (T)	TO-92 (L)		
3	2	2	1	V_{IN}	Supply Voltage Input
2	3	3	2	V_{SS}	Ground
1	1	1	3	V_{OUT}	Output

■PRODUCT CLASSIFICATION

●Ordering Information

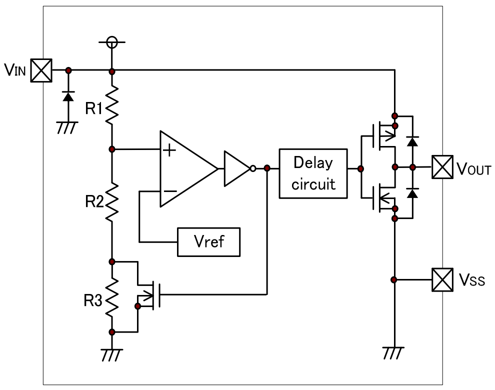
XC61F ①②③④⑤⑥⑦-⑧[*1]

DESIGNATOR	DESCRIPTION	SYMBOL	DESCRIPTION
①	Output Configuration	C	CMOS output
		N	N-ch open drain output
② ③	Detect Voltage	16 ~ 60	e.g. 2.5V → ②2 , ③5
			e.g. 3.8V → ②3, ③8
④	Release Output Delay	1	50ms ~ 200ms
		4	80ms ~ 400ms
		5	1ms ~ 50ms
⑤	Detect Accuracy	2	Within ± 2.0%
⑥⑦-⑧	Packages Taping Type [*2]	MR	SOT-23
		MR-G	SOT-23 (Halogen & Antimony free)
		PR	SOT-89
		PR-G	SOT-89 (Halogen & Antimony free)
		TH	TO-92 (Standard): Paper type
		TB	TO-92 (Standard): Bag
		LH	TO-92 (Custom pin configuration): Paper type (Discontinued Product)
		LB	TO-92 (Custom pin configuration): Bag (Discontinued Product)

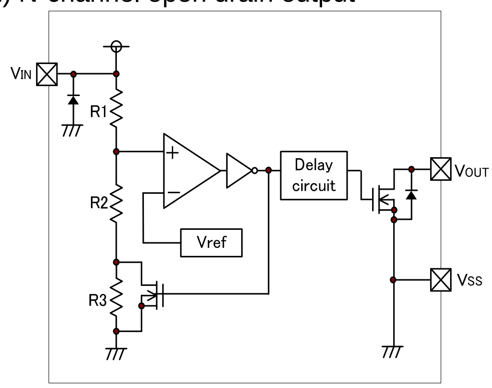
[*1] The "-G" suffix indicates that the products are Halogen and Antimony free as well as being fully RoHS compliant.
[*2] The device orientation is fixed in its embossed tape pocket. For reverse orientation, please contact your local Torex sales office or representative. (Standard orientation: ⑥R-⑧, Reverse orientation: ⑥L-⑧)

■BLOCK DIAGRAMS

(1) CMOS output



(2) N-channel open drain output



■ABSOLUTE MAXIMUM RATINGS

Ta = 25℃

PARAMETER		SYMBOL	RATINGS	UNITS
Input Voltage		VIN	12.0	V
Output Current		IOUT	50	mA
Output Voltage	CMOS	VOUT	VSS -0.3 ~ VIN + 0.3	V
	N-ch open drain		VSS -0.3 ~ 9	
Power Dissipation	SOT-23	Pd	250	mW
	SOT-89		500	
	TO-92		300	
Operating Temperature Range		Topr	-30～+85	℃
Storage Temperature Range		Tstg	-40～+125	℃

■ELECTRICAL CHARACTERISTICS

Ta = 25℃

PARAMETER		SYMBOL	CONDITIONS		MIN.	TYP.	MAX.	UNITS	CIRCUIT
Detect Voltage		VDF			VDF(T) x 0.98	VDF(T)	VDF(T) x 1.02	V	①
Hysteresis Width		VHYS			VDF x 0.02	VDF x 0.05	VDF x 0.08	V	①
Supply Current		ISS		VIN = 1.5V	-	0.9	2.6	μA	②
				VIN = 2.0V	-	1.0	3.0		
				VIN = 3.0V	-	1.3	3.4		
				VIN = 4.0V	-	1.6	3.8		
				VIN = 5.0V	-	2.0	4.2		
Operating Voltage		VIN	VDF= 1.6V to 6.0V		0.7	-	10.0	V	①
Output Current		IOUT	N-ch VDS =0.5V	VIN = 1.0V	1.0	2.2	-	mA	③
				VIN = 2.0V	3.0	7.7	-		
				VIN = 3.0V	5.0	10.1	-		
				VIN = 4.0V	6.0	11.5	-		
				VIN = 5.0V	7.0	13.0	-		
			P-ch VDS=2.1V (CMOS Output)	VIN = 8.0V	-	-10.0	-2.0		④
Leak Current	CMOS Output	Ileak	VIN = 10.0V，VOUT = 10.0V		-	0.01	-	μA	③
	Nch Open Drain				-	0.01	0.1		
Detect Voltage Temperature Characteristics		ΔVDF / ΔTopr・VDF			-	±100	-	ppm/℃	-
Release Delay Time (VDR → VOUT inversion)		TDLY*	VIN changes from 0.6V to 10V		50	-	200	ms	⑤
					80		400		
					1		50		

VDF (T): Setting detect voltage value
Release Voltage: VDR = VDF + VHYS
* Release Delay Time: 1ms to 50ms & 80ms to 400ms versions are also available.
Note: The power consumption during power-start to output being stable (release operation) is 2μA greater than it is after that period (completion of release operation) because of delay circuit through current.

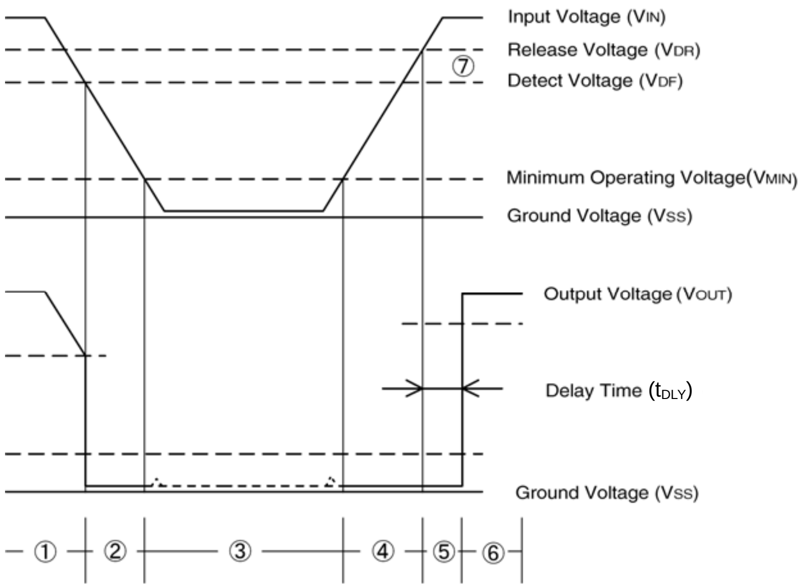
■OPERATIONAL EXPLANATION

●CMOS output

① When a voltage higher than the release voltage (VDR) is applied to the voltage input pin (VIN), the voltage will gradually fall. When a voltage higher than the detect voltage (VDF) is applied to VIN, output (VOUT) will be equal to the input at VIN.
Note that high impedance exists at VOUT with the N-channel open drain configuration. If the pin is pulled up, VOUT will be equal to the pull up voltage.
② When VIN falls below VDF, VOUT will be equal to the ground voltage (VSS) level (detect state). Note that this also applies to N-channel open drain configurations.
③ When VIN falls to a level below that of the minimum operating voltage (VMIN) output will become unstable. Because the output pin is generally pulled up with N-channel open drain configurations, output will be equal to pull up voltage.
④ When VIN rises above the VSS level (excepting levels lower than minimum operating voltage), VOUT will be equal to VSS until VIN reaches the VDR level.
⑤ Although VIN will rise to a level higher than VDR, VOUT maintains ground voltage level via the delay circuit.
⑥ Following transient delay time, VIN will be output at VOUT. Note that high impedance exists with the N-channel open drain configuration and that voltage will be dependent on pull up.

Notes:
1. The difference between VDR and VDF represents the hysteresis range.
2. Release delay time (t_{DLY}) represents the time it takes for VIN to appear at VOUT once the said voltage has exceeded the VDR level.

●Timing Chart



■DIRECTIONS FOR USE

●Notes on Use

1. Please use this IC within the stated maximum ratings. The IC is liable to malfunction should the ratings be exceeded.
2. When a resistor is connected between the V_{IN} pin and the input with CMOS output configurations, oscillation may occur as a result of voltage drops at R_{IN} if load current (I_{OUT}) exists. It is therefore recommend that no resistor be added. (refer to Oscillation Description (1) below)
3. When a resistor is connected between the V_{IN} pin and the input with CMOS output configurations, irrespective of N-ch output configurations, oscillation may occur as a result of through current at the time of voltage release even if load current (I_{OUT}) does not exist. (refer to Oscillation Description (2) below)
4. With a resistor connected between the V_{IN} pin and the input, detect and release voltage will rise as a result of the IC's supply current flowing through the V_{IN} pin.
5. If a resistor (R_{IN}) must be used, then please use with as small a level of input impedance as possible in order to control the occurrences of oscillation as described above.
   Further, please ensure that R_{IN} is less than 10kΩ and that C_{IN} is more than 0.1μF (Figure 1). In such cases, detect and release voltages will rise due to voltage drops at R_{IN} brought about by the IC's supply current.
6. Depending on circuit's operation, transient delay time of this IC can be widely changed due to upper limits or lower limits of operational ambient temperature.

●Oscillation Description

(1) Oscillation as a result of output current with the CMOS output configuration:

When the voltage applied at IN rises, release operations commence and the detector's output voltage increases. Load current (I_{OUT}) will flow through R_L. Because a voltage drop (R_{IN} x I_{OUT}) is produced at the R_{IN} resistor, located between the input (IN) and the V_{IN} pin, the load current will flow via the IC's V_{IN} pin. The voltage drop will also lead to a fall in the voltage level at the V_{IN} pin. When the V_{IN} pin voltage level falls below the detect voltage level, detect operations will commence. Following detect operations, load current flow will cease and since voltage drop at R_{IN} will disappear, the voltage level at the V_{IN} pin will rise and release operations will begin over again.

Oscillation may occur with this " release - detect - release " repetition.

Further, this condition will also appear via means of a similar mechanism during detect operations.

(2) Oscillation as a result of through current:

Since the XC61F series are CMOS ICs, through current will flow when the IC's internal circuit switching operates (during release and detect operations). Consequently, oscillation is liable to occur during release voltage operations as a result of output current which is influenced by this through current (Figure 3).

Since hysteresis exists during detect operations, oscillation is unlikely to occur.

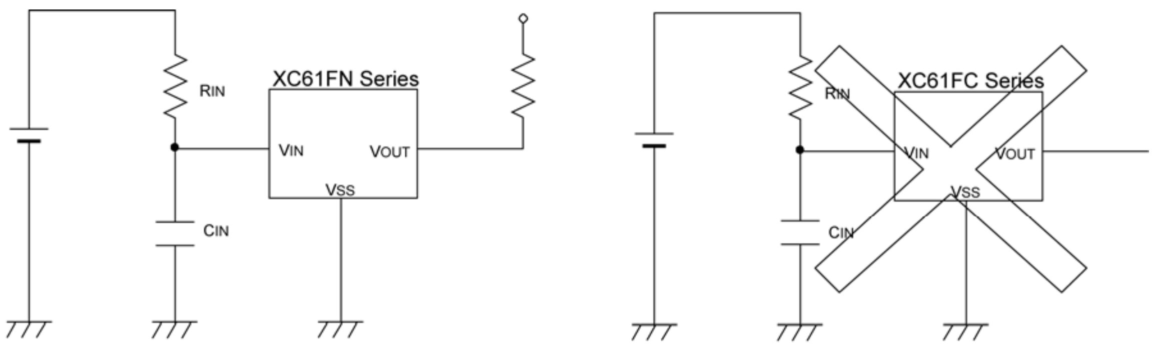


Figure 1. When using an input resistor

■DIRECTIONS FOR USE (Continued)

●Oscillation Description (Continued)

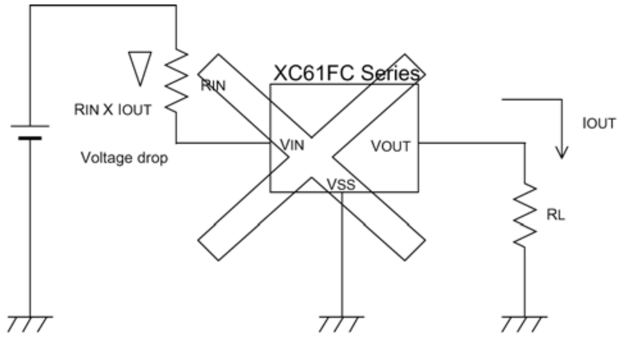


Figure 2. Oscillation in relation to output current

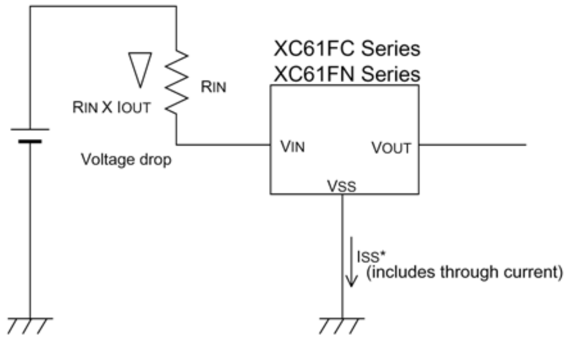
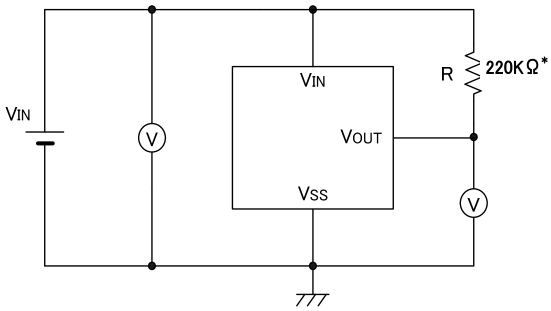


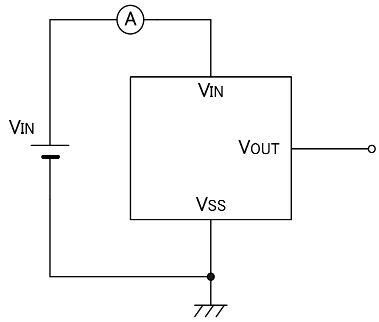
Figure 3. Oscillation in relation to through current

■TEST CIRCUITS

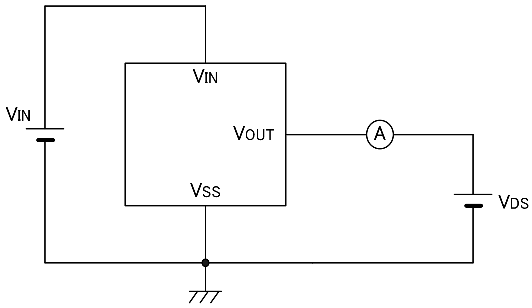
●Circuit ①



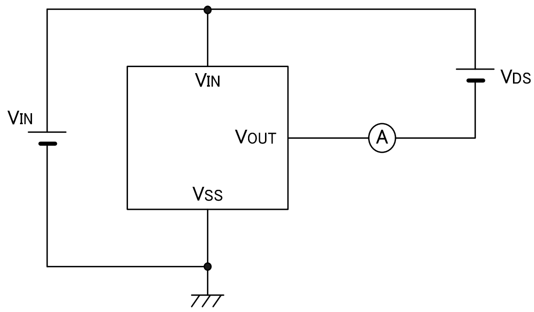
●Circuit ②



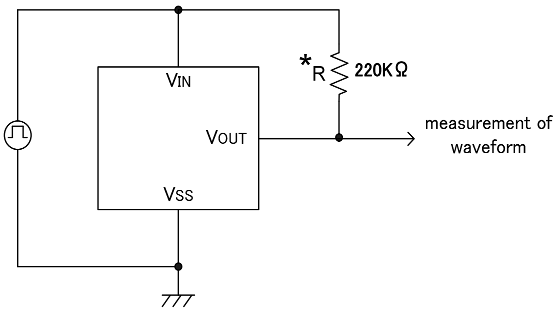
●Circuit ③



●Circuit ④



●Circuit ⑤

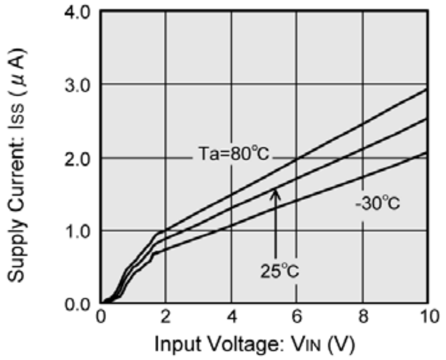


*Not necessary with CMOS output products.

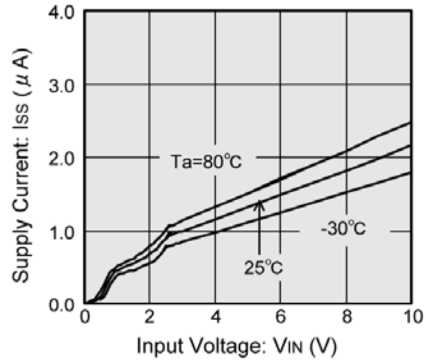
■TYPICAL PERFORMANCE CHARACTERISTICS

(1) Supply Current vs. Input Voltage

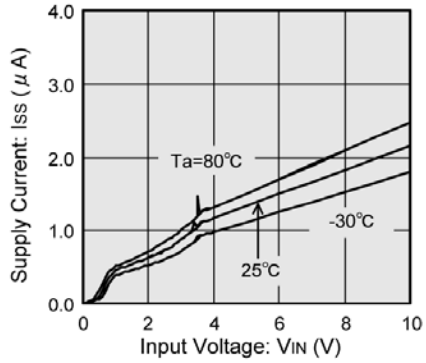
XC61FN1612



XC61FN2512

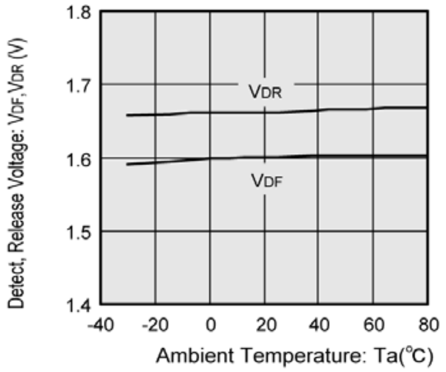


XC61FN3512

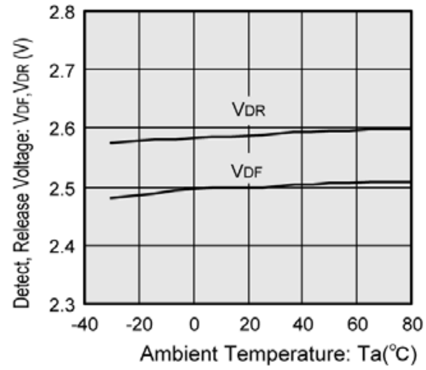


(2) Detect Voltage, Release Voltage vs. Ambient Temperature

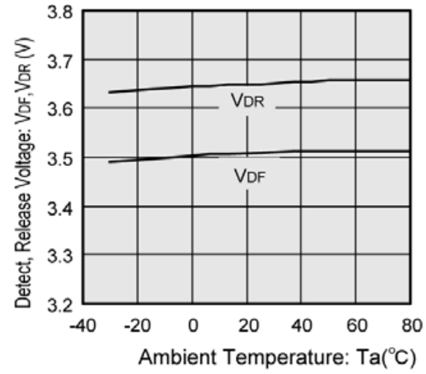
XC61FN1612



XC61FN2512

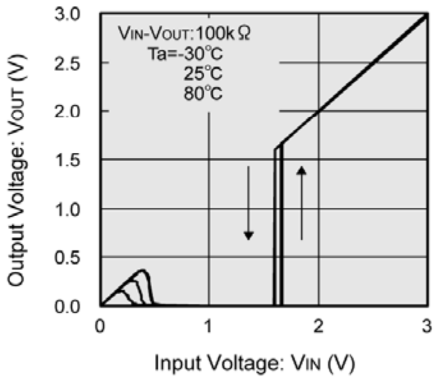


XC61FN3512



(3) Output Voltage vs. Input Voltage

XC61FN1612



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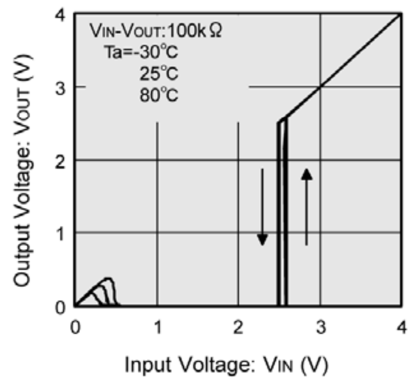

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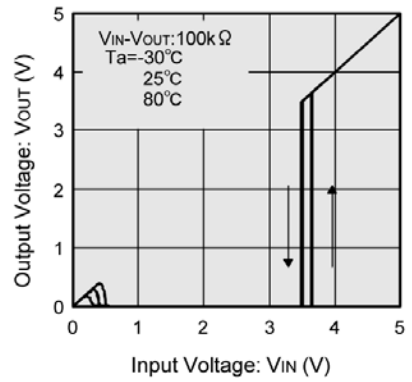
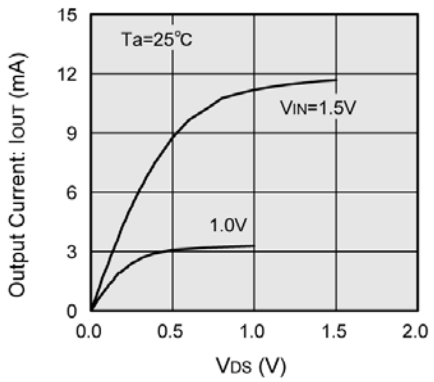


(4) N-Channel Driver Output Current vs. VDS

XC61FN1612



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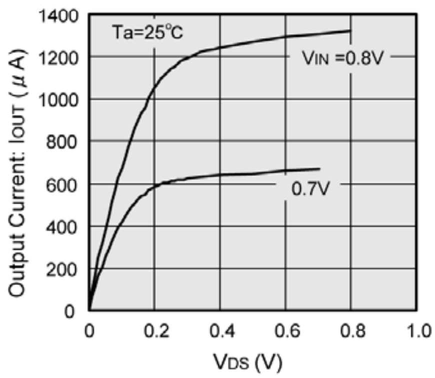

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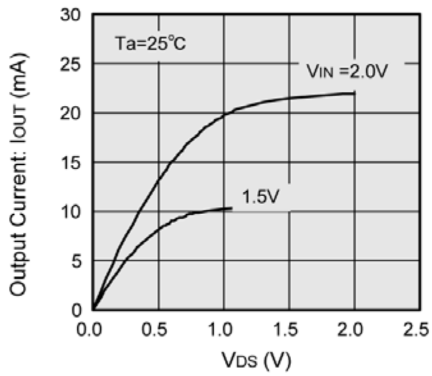
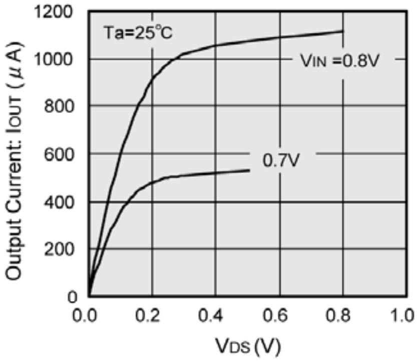


■TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

(4) N-Channel Driver Output Current vs. VDS (Continued)

XC61FN2512



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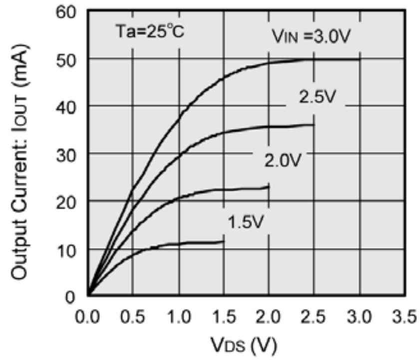

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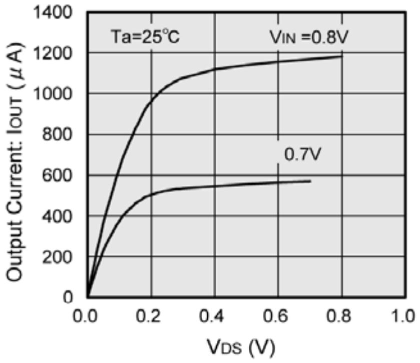
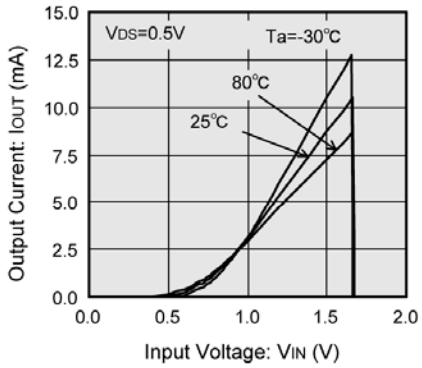


(5) N-Channel Driver Output Current vs. Input Voltage

XC61FN1612



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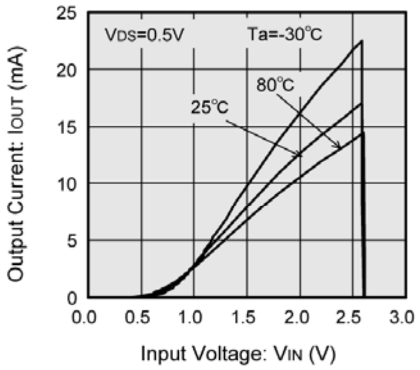

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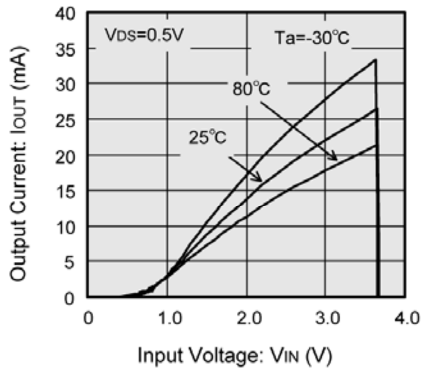
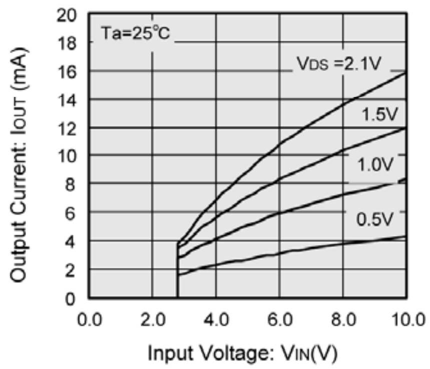
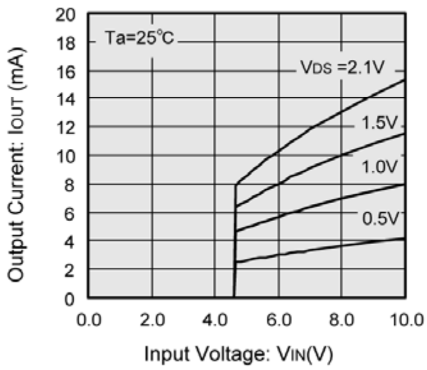


(6) P-Channel Driver Output Current vs. Input Voltage

XC61FC2712

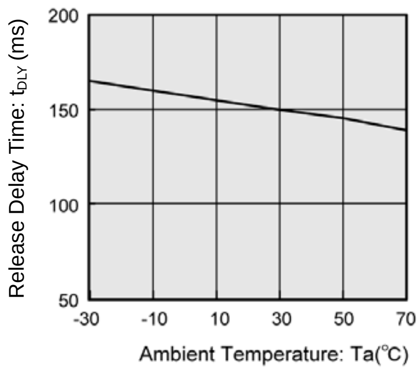


XC61FC4412

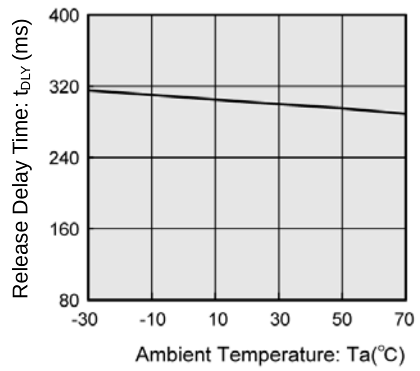


(7) Release Delay Time vs. Ambient Temperature

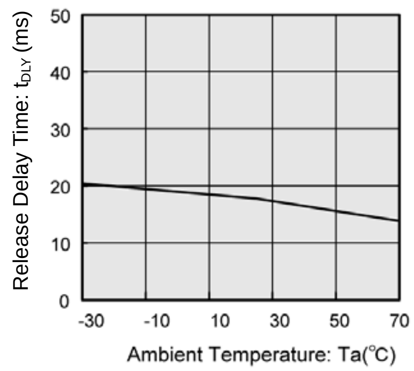
XC61FC3012



XC61FC3042

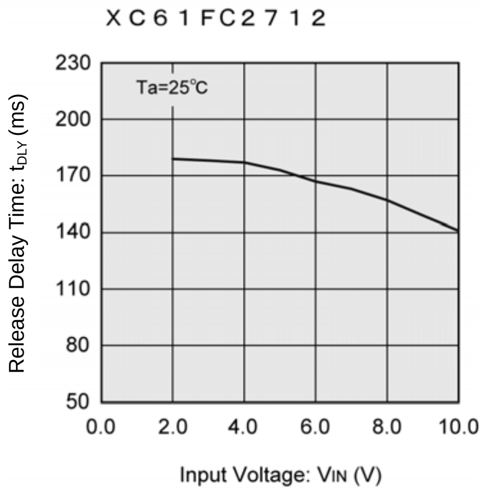


XC61FC3052



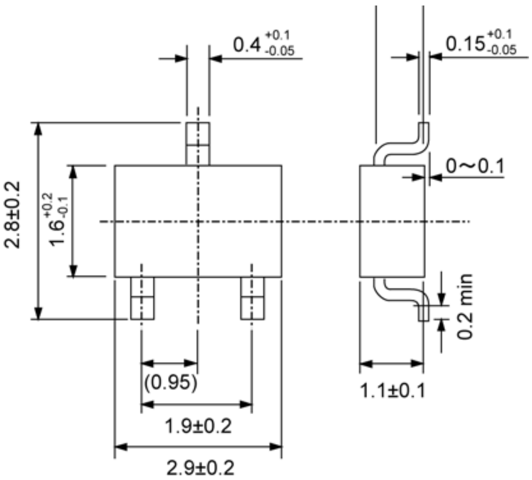
■TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

(8) Release Delay Time vs. Input Voltage

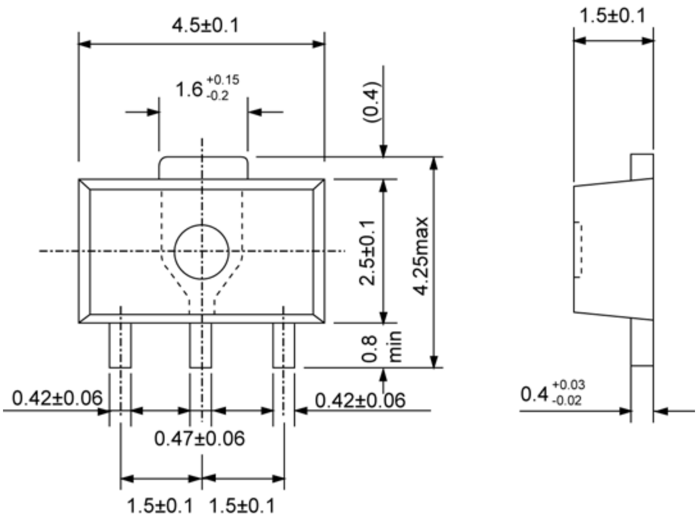


■PACKAGING INFORMATION

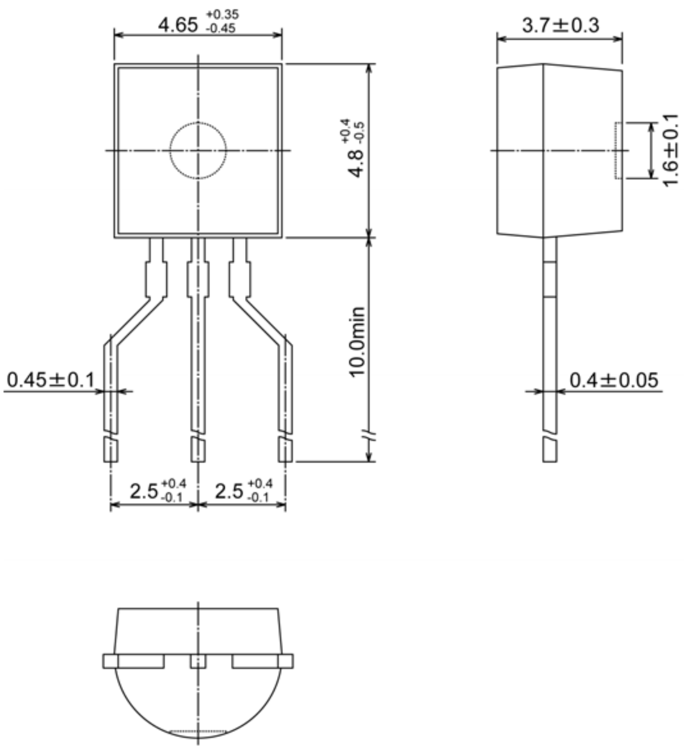
●SOT-23



●SOT-89

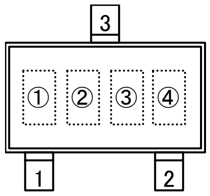


●TO-92

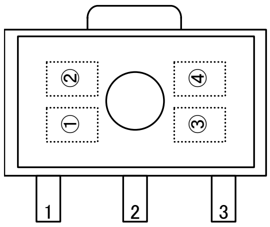


■MARKING RULE

●SOT-23, SOT-89



SOT-23
(TOP VIEW)



SOT-89
(TOP VIEW)

①Represents integer of detect voltage and output configuration

CMOS output (XC61FC series)

MARK	CONFIGURATION	VOLTAGE (V)
A	CMOS	0.x
B	CMOS	1.x
C	CMOS	2.x
D	CMOS	3.x
E	CMOS	4.x
F	CMOS	5.x
H	CMOS	6.x

N-channel open drain (XC61FN series)

MARK	CONFIGURATION	VOLTAGE (V)
K	N-ch	0.x
L	N-ch	1.x
M	N-ch	2.x
N	N-ch	3.x
P	N-ch	4.x
R	N-ch	5.x
S	N-ch	6.x

②Represents decimal number of detect voltage

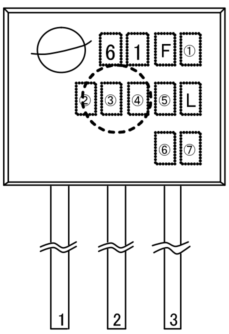
MARK	VOLTAGE (V)	MARK	VOLTAGE (V)
0	x.0	5	x.5
1	x.1	6	x.6
2	x.2	7	x.7
3	x.3	8	x.8
4	x.4	9	x.9

③Represents delay time

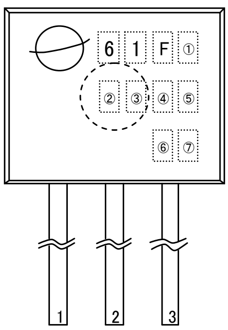
VOLTAGE (V)	DELAY TIME
5	50 ~ 200ms
6	80 ~ 400ms
7	1 ~ 50ms

④Represents assembly lot number (Based on internal standards)

●TO-92



TO-92 (L Type)
(TOP VIEW)



TO-92 (T Type)
(TOP VIEW)

①Represents output configuration

MARK	OUTPUT CONFIGURATION
C	CMOS
N	N-ch

②, ③Represents detect voltage

MARK		VOLTAGE (V)
②	③	
3	3	3.3
5	0	5.0

④Represents delay time

MARK	DELAY TIME
1	50ms ~ 200ms
4	80ms ~ 400ms
5	1ms ~ 50ms

⑤Represents detect voltage accuracy

MARK	DETECT VOLTAGE ACCURACY
2	Within ±2%

⑥Represents a least significant digit of the production year (ex.)

MARK	PRODUCTION YEAR
3	2003
4	2004

⑦Represents production lot number

0 to 9, A to Z repeated (G, I, J, O, Q, W expected)

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2. We assume no responsibility for any infringement of patents, patent rights, or other rights arising from the use of any information and circuitry in this datasheet.
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